



Preliminary data

SPI21N10
SPP21N10, SPB21N10

SIPMOS® Power-Transistor

Feature

- N-Channel
- Enhancement mode
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

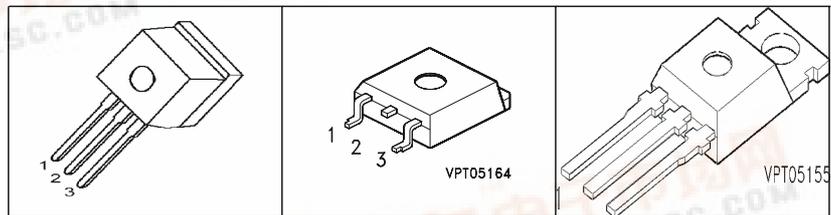
Product Summary

V_{DS}	100	V
$R_{DS(on)}$	80	mΩ
I_D	21	A

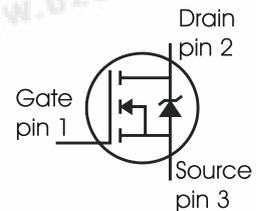
P-TO262-3-1

P-TO263-3-2

P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP21N10	P-TO220-3-1	Q67042-S4116	21N10
SPB21N10	P-TO263-3-2	Q67042-S4102	21N10
SPI21N10	P-TO262-3-1	Q67042-S4117	21N10



Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	21	A
$T_C=25\text{ }^\circ\text{C}$		21	
$T_C=100\text{ }^\circ\text{C}$		15.0	
Pulsed drain current	$I_{D\text{ puls}}$	84	
$T_C=25\text{ }^\circ\text{C}$			
Avalanche energy, single pulse	E_{AS}	130	mJ
$I_D=21\text{ A}$, $V_{DD}=25\text{ V}$, $R_{GS}=25\text{ }\Omega$			
Reverse diode dv/dt	dv/dt	6	kV/ μs
$I_S=21\text{ A}$, $V_{DS}=80\text{ V}$, $di/dt=200\text{ A}/\mu\text{s}$, $T_{j\text{ max}}=175\text{ }^\circ\text{C}$			
Gate source voltage	V_{GS}	± 20	V
Power dissipation	P_{tot}	90	W
$T_C=25\text{ }^\circ\text{C}$			
Operating and storage temperature	T_j, T_{stg}	-55... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/175/56	



Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	1.7	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ^{F)}	R_{thJA}	-	-	62 40	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=1mA$	$V_{(BR)DSS}$	100	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 44\ \mu A$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS}=100V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=100V, V_{GS}=0V, T_j=125^\circ C$	I_{DSS}	-	0.01 1	1 100	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	1	100	
Drain-source on-state resistance $V_{GS}=10V, I_D=15.0A$	$R_{DS(on)}$	-	65	80	$m\Omega$

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 * I_D * R_{DS(on)max}$, $I_D = 15.0\text{A}$	6.5	12.4	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	650	865	pF
Output capacitance	C_{oss}		-	140	186	
Reverse transfer capacitance	C_{rss}		-	80	120	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 21\text{A}$, $R_G = 13\Omega$	-	10	15	ns
Rise time	t_r		-	56	84	
Turn-off delay time	$t_{d(off)}$		-	37	55	
Fall time	t_f		-	23	35	

Gate Charge Characteristics

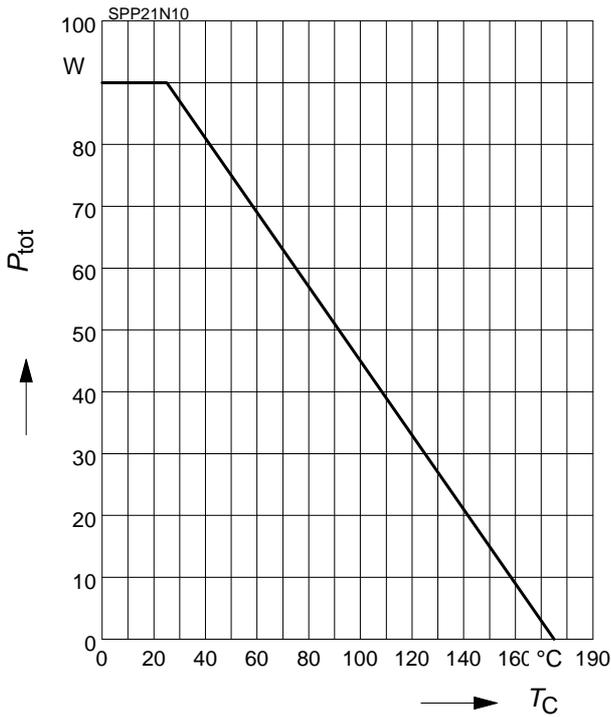
Gate to source charge	Q_{gs}	$V_{DD} = 80\text{V}$, $I_D = 21\text{A}$	-	3.9	5.2	nC
Gate to drain charge	Q_{gd}		-	15.5	23.3	
Gate charge total	Q_g	$V_{DD} = 80\text{V}$, $I_D = 21\text{A}$, $V_{GS} = 0$ to 10V	-	28.9	38.4	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 80\text{V}$, $I_D = 21\text{A}$	-	6.2	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	21	A
Inverse diode direct current, pulsed	I_{SM}		-	-	84	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_F = 21\text{A}$	-	0.94	1.25	V
Reverse recovery time	t_{rr}	$V_R = 50\text{V}$, $I_F = I_S$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	65	81.5	ns
Reverse recovery charge	Q_{rr}		-	153	192	

1 Power dissipation

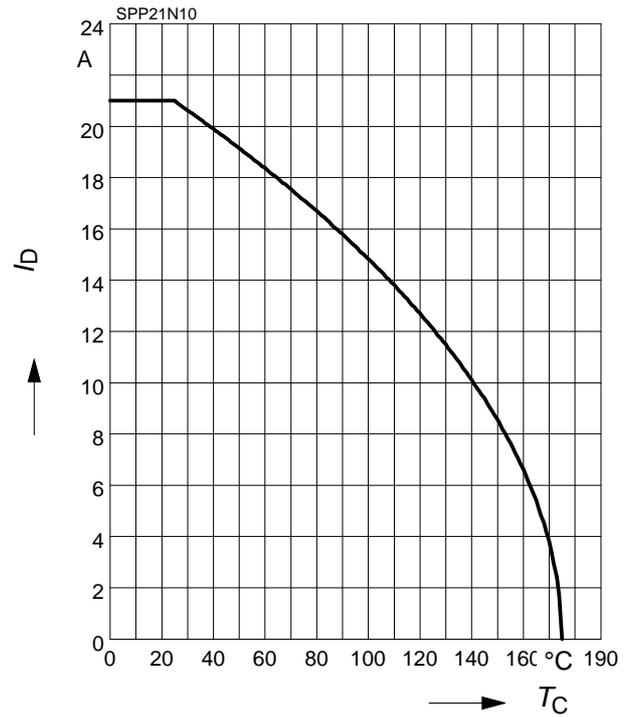
$$P_{tot} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

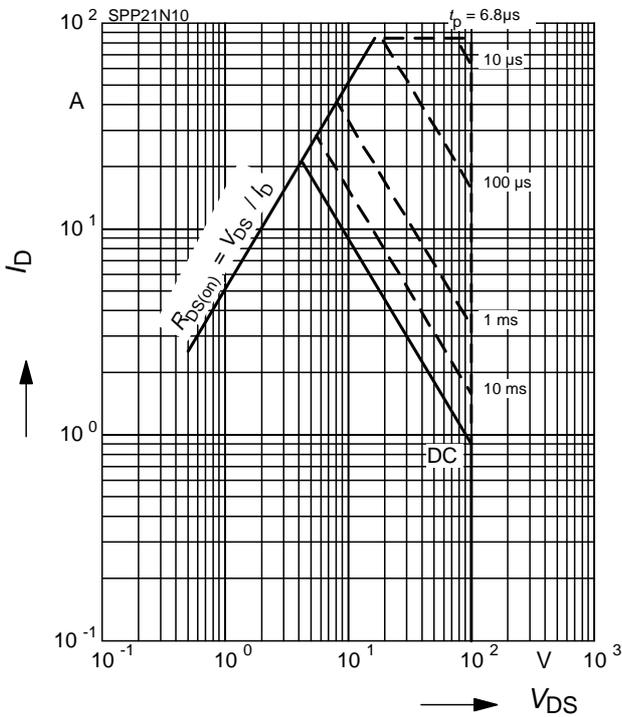
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

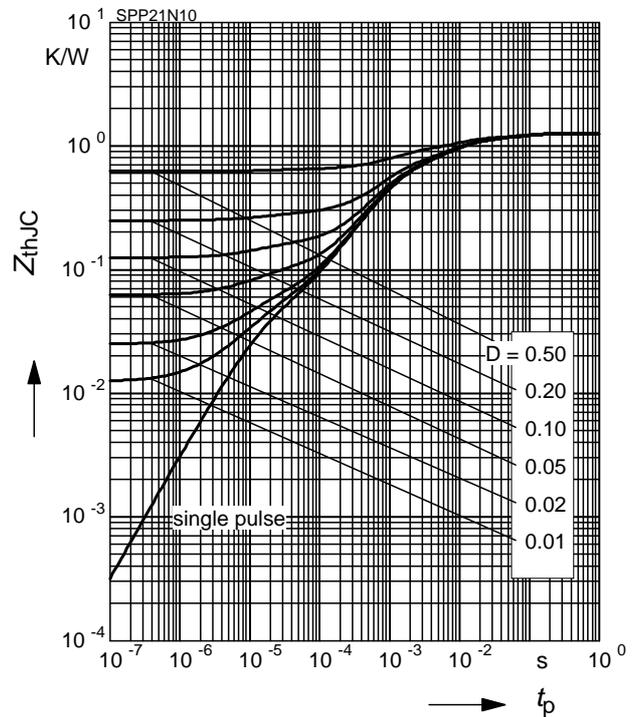
parameter: $D = 0, T_C = 25 \text{ °C}$



4 Transient thermal impedance

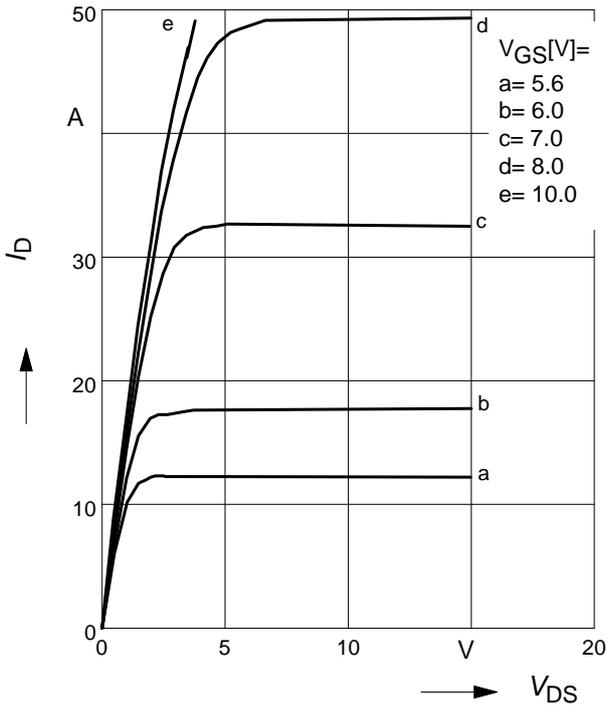
$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p / T$



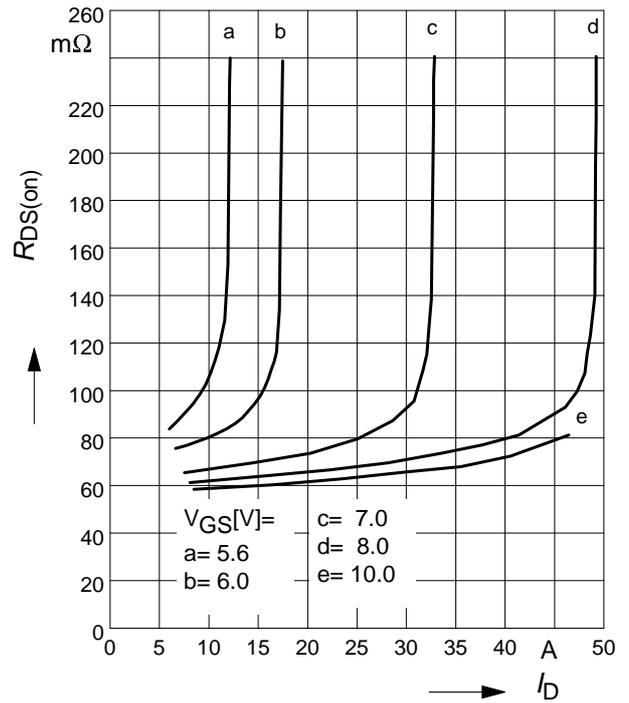
5 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$
parameter: $t_p = 80 \mu\text{s}$



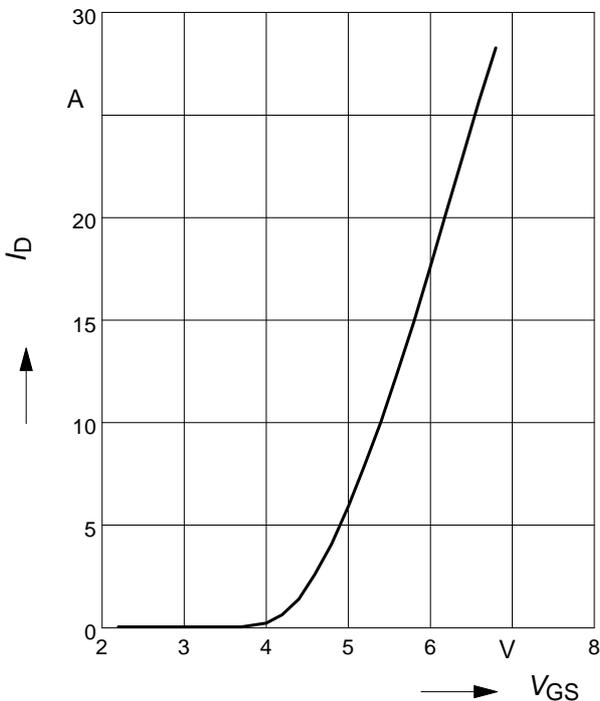
6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$
parameter: V_{GS}



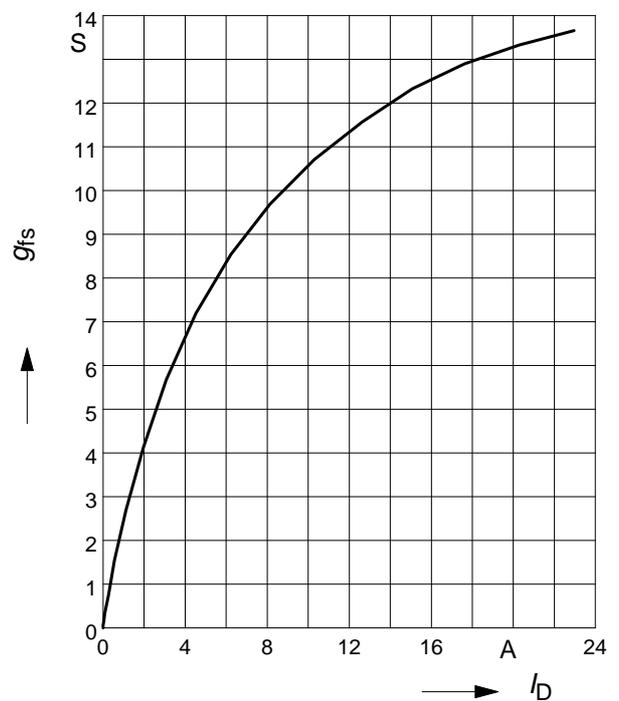
7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

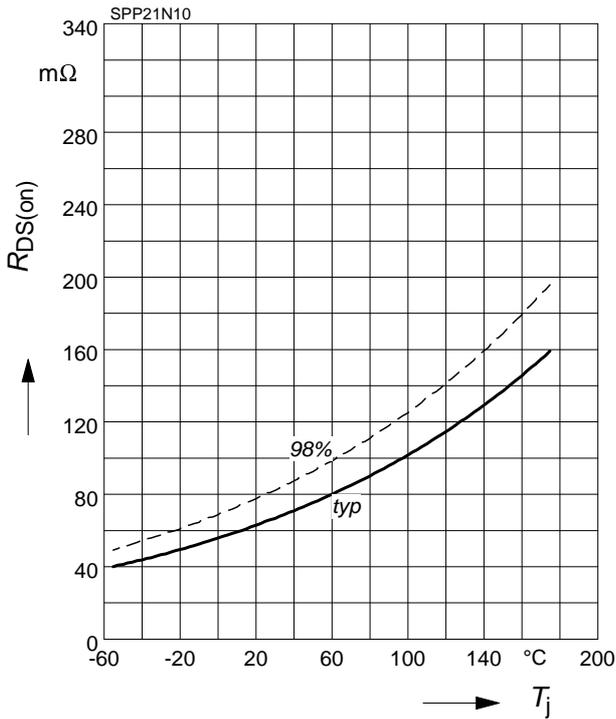
$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

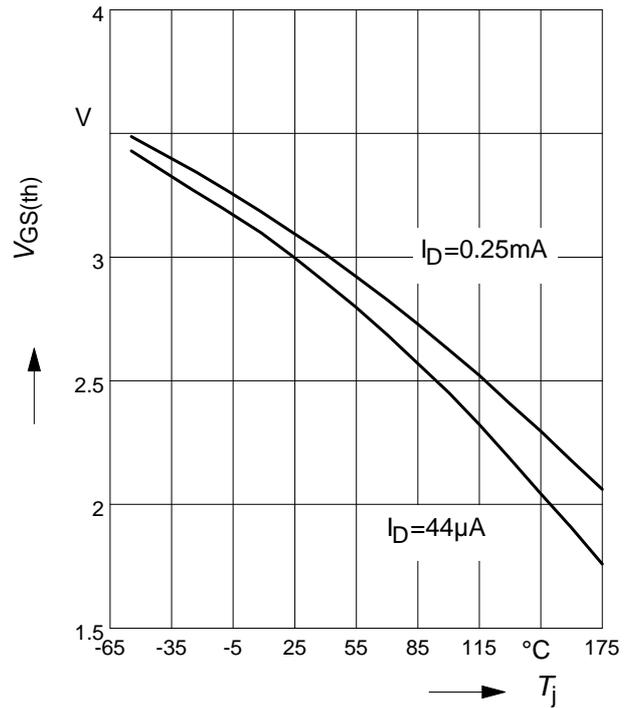
parameter : $I_D = 15.0 \text{ A}$, $V_{GS} = 10 \text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

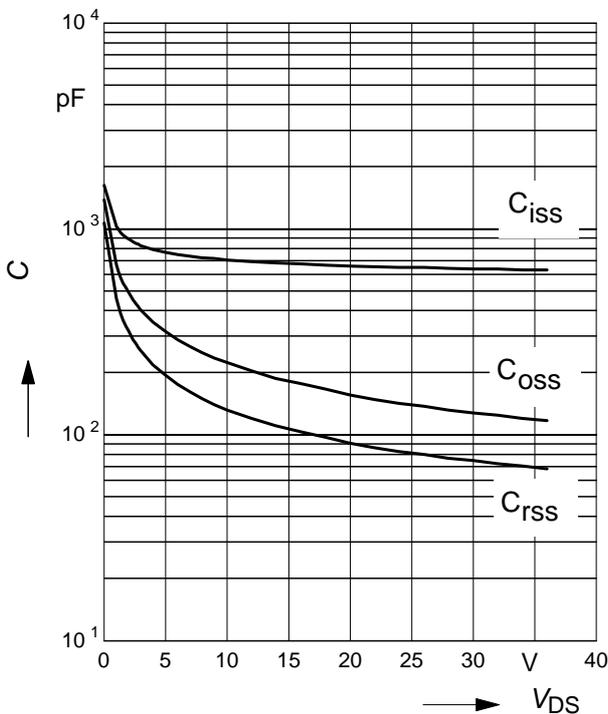
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

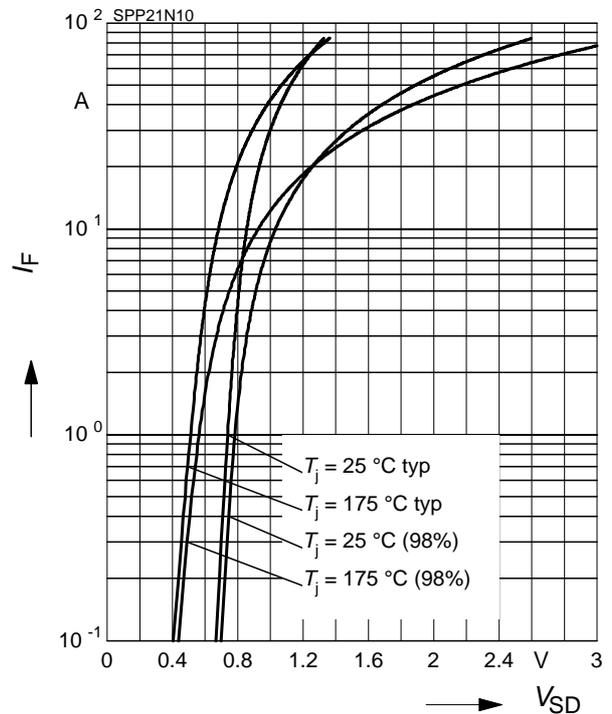
parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

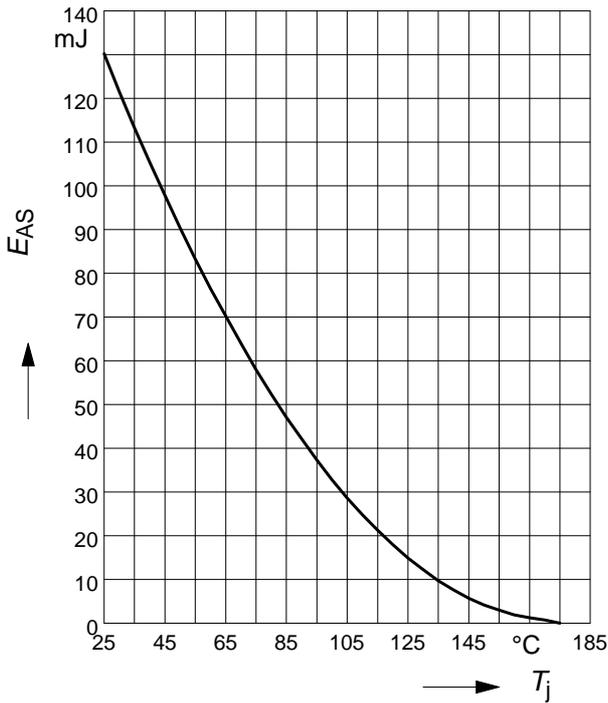
parameter: T_j , $t_p = 80 \mu\text{s}$



13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

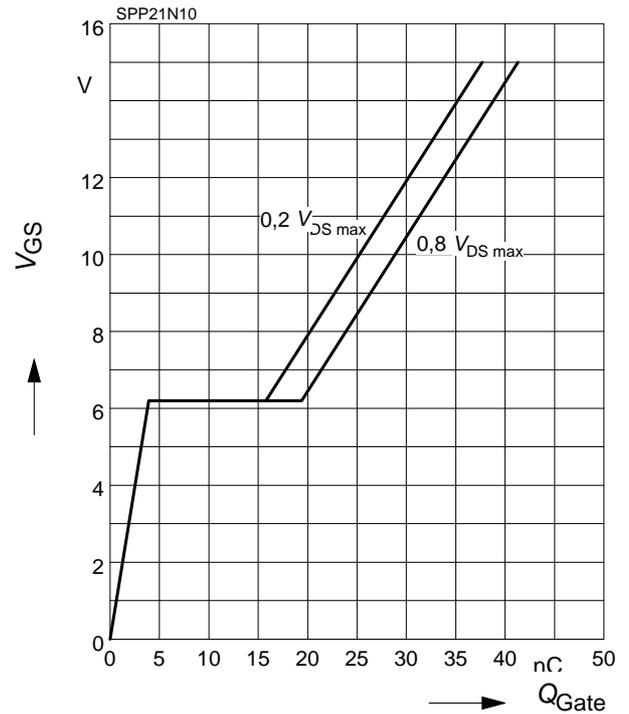
par.: $I_D = 21\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\ \Omega$



14 Typ. gate charge

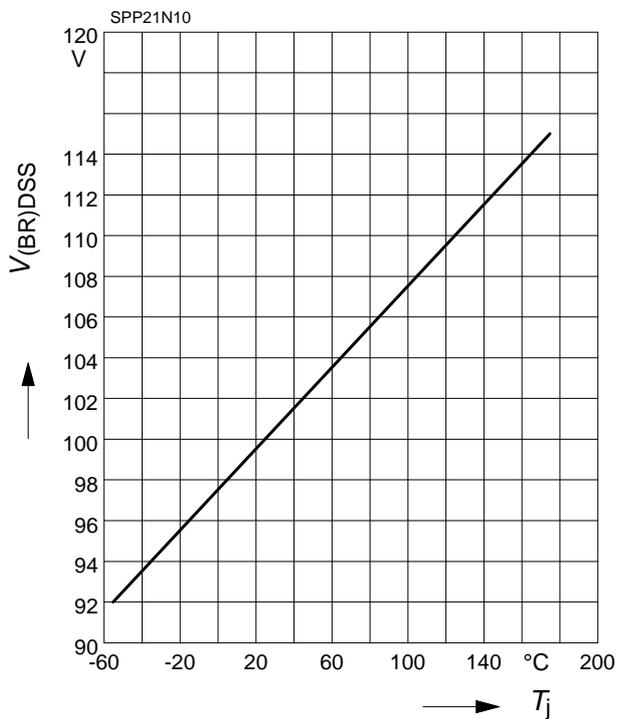
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = 21\text{ A}$ pulsed



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$





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